MENU SEARCH INDEX DETAIL

1/1



PATENT ABSTRACTS OF JAPAN

(11)Publication number: 11150300

(43)Date of publication of application: 02.06.1999

(51)Int.CI.

H01L 33/00 H01S 3/18

(21)Application number: 09331022

(22) Date of filing: 14.11.1997

(71)Applicant:

(72)Inventor:

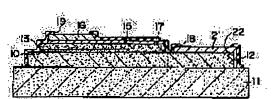
NICHIA CHEM IND LTD TOYODA TATSUNORI NAKAGAWA YOSHINORI

KUSUSE TAKESHI

(54) NITRIDE SEMICONDUCTOR ELEMENT

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a nitride semiconductor element, in which an electric current can be injected uniformly into a light-emitting layer (or light-receiving layer), and which can be improved in luminous efficiency (or light-receiving efficiency). SOLUTION: A nitride semiconductor element is provided with a first semiconductor layer 12 which is formed on a substrate 11 and composed of an n-type nitride semiconductor, a second semiconductor layer 13 formed on the layer 12 with an operating region in between and composed of a p-type nitride semiconductor, a positive electrode 15 formed on the layer 13, and a negative electrode 21 formed on the surface of the layer 12 exposed by removing a part of the layer 13. The exposed surface of the first semiconductor layer 12 which is exposed so as to form the negative electrode 21 continuously exposed from a part of its outer peripheral side face, and the negative electrode 21 is formed continuously from the exposed surface to the continuous outer peripheral side face of the first semiconductor layer 12.



LEGAL STATUS

[Date of request for examination]

06.03.2000

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998 Japanese Patent Office

